

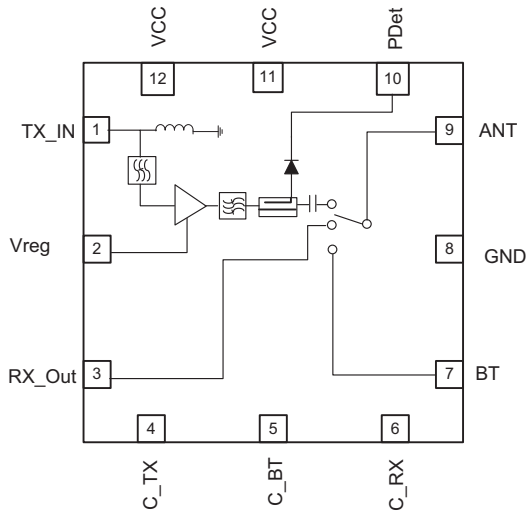


Features

- Integrated 2.4GHz to 2.4GHz b/g/n Amplifier, SP3T Switch, and Power Detector Coupler
- Single Supply Voltage 3.0V to 4.8V
- Output Power: 11b=21dBm Meeting Spectral Mask
11n=18dBm at <2.5% EVM
- Low Height Package, Suited for SiP and CoB Designs

Applications

- Cellular handsets
- Mobile devices
- Tablets
- Consumer electronics
- Gaming
- Netbooks/Notebooks
- TV/monitors/video
- SmartEnergy



Functional Block Diagram

Product Description

The RF5375 provides an integrated front end solution for WiFi 802.11b/g/n and Bluetooth® systems. The ultra-small form factor package and integrated matching greatly reduces the number of external components and layout area in the customer application. This simplifies the total front end solution by reducing the bill of materials, system footprint, and assembly cost.

The RF5375 integrates a 2.4GHz power amplifier (PA), 2170MHz notch filter for coexistence with cellular radios, second harmonic attenuation, power detector coupler for improved accuracy, and an SP3T switch capable of simultaneous reception for WiFi and Bluetooth®. The device is provided in a 2.5mmx2.5mmx0.5mm, 12-pin package. This module meets or exceeds the RF front end needs of IEEE 802.11b/g/n WiFi RF systems.

Ordering Information

| | |
|---------------|--|
| RF5375SQ | Standard 25 piece bag |
| RF5375SR | Standard 100 piece reel |
| RF5375TR7 | Standard 2500 piece reel |
| RF5375PCK-410 | Fully Assembled Evaluation Board with 5 piece Sample |

Optimum Technology Matching® Applied

- | | | | |
|---|--------------------------------------|--|-----------------------------------|
| <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input checked="" type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | <input type="checkbox"/> RF MEMS |
| <input checked="" type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | <input type="checkbox"/> LDMOS |

Absolute Maximum Ratings

| Parameter | Rating | Unit |
|---|--------------|-----------------|
| Supply Voltage | -0.5 to +5.4 | V _{DC} |
| PA Regulated Voltage (V _{REG}) | -0.5 to 3.5 | V _{DC} |
| DC Supply Current | 500 | mA |
| Maximum TX and RX Input Power (no damage) | 0 | dBm |
| Operating Case Temperature | -40 to +85 | °C |
| Storage Temperature | -40 to +150 | °C |
| Moisture Sensitivity | MSL2 | |



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

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| Parameter | Specification | | | Unit | Condition | |
|--------------------------|---------------------|------|------|------|--|--|
| | Min. | Typ. | Max. | | | |
| Compliance | | | | | IEEE802.11b/g/n Standards; FCC CFG 15.247, .205, .209; EN and JDEC. | |
| Operating Conditions | | | | | V _{CC} =3.0V to 4.8V; V _{REG} =2.8V to 2.9V; Switch Control voltage=2.7V to 3.6V; Temp=-10 °C to +70 °C (Spec Compliant); Temp=-40 °C to -10 °C and +70 °C to +85 °C (Reduced Performance); Unless noted otherwise | |
| Frequency Range | 2.4 | | 2.5 | GHz | | |
| Power Supply | 3.0 | 3.3 | 4.8 | V | | |
| | 2.7 | | | V | Derated performance | |
| V _{REG} Voltage | | | | | | |
| | ON | 2.80 | 2.85 | 2.90 | V | PA in "ON" state |
| | OFF | 0 | | 0.2 | V | PA in "OFF" state |
| Output Power | | | | | | |
| | 11n | 16.5 | 17 | | dBm | V _{CC} ≥3.0V OFDM 54Mbps |
| | 11n | 17.5 | 18 | | dBm | V _{CC} ≥3.3V OFDM 54Mbps |
| | 11g | 18 | 18.5 | | dBm | V _{CC} ≥3.3V OFDM 54Mbps |
| | 11b | 19.5 | 21 | | dBm | 11Mbps, CCK, V _{CC} ≥3.3V |
| EVM | | | | | | |
| | 11g | | | 4 | % | 18dBm, OFDM 54Mbps, V _{CC} =3.3V to 4.8V, all temperature |
| | 11n | | 2.5 | 3.0 | % | 17.5dBm, OFDM 54Mbps, V _{CC} =3.3V to 4.8V, all temperature |
| | | | | 3.0 | % | 16.5dBm, OFDM 54Mbps, V _{CC} =3.0V _{DC} , all temperature |
| Adjacent Channel Power | | | | | | P _{OUT} =21Bm, V _{CC} =3.3v, 11Mbps CCK signal. See note 2 |
| | ACP1 | | -36 | -33 | dBc | +/- 11MHz Offset from carrier |
| | ACP2 | | -56 | -52 | dBc | +/- 22MHz Offset from carrier |
| Gain | 23 | 25 | 29 | | dB | At rated P _{OUT} |
| Gain Variance Slope | | | | | | |
| | Channel 40MHz BW | -1.0 | | +1.0 | dB | |
| | Channel 20MHz BW | -0.5 | | +0.5 | dB | |
| | Frequency 100MHz BW | -2 | | +2 | dB | In-Band variance 2.4GHz to 2.5GHz |
| Out of Band Rejection | | | | | | |
| | 2170MHz | 6 | 8 | | dBc | CW Signal |

| Parameter | Specification | | | Unit | Condition |
|--|---------------|------|------|-----------------|---|
| | Min. | Typ. | Max. | | |
| Compliance, cont. | | | | | |
| Power Detector | | | | | |
| Output Power Range | 0 | | 23 | dBm | |
| Voltage Range | 0.1 | | 1.5 | V _{DC} | |
| Voltage at P _{OUT} =18dBm | 0.6 | 0.65 | 0.7 | dB | 11g; 50Ω; V _{CC} =3.0V to 4.8V |
| Filter Bandwidth | | 0.1 | | MHz | |
| Sensitivity | | | | | |
| P _{OUT} <.5V | 10 | | | mV/dB | |
| P _{OUT} >.5V | 20 | | | mV/dB | |
| Voltage Target at 23dBm P _{OUT} | | 1.2 | | V | V _{CC} =3.3v, Temp=25 °C |
| Load Variation | | | ±200 | mV | up to 3:1 VSWR |
| Current Consumption | | | | | |
| Quiescent | | 135 | 180 | mA | V _{CC} =3.0V to 4.8V, All Temp |
| Operating | | 170 | 200 | mA | V _{CC} ≤4.2V _{DC} , P _{OUT} =18dBm, 11n, 50Ω, Temp=25 °C |
| Operating | | | 220 | mA | V _{CC} ≤4.8V _{DC} , P _{OUT} =17.5 dBm, 11n, 50Ω, All Temp |
| Operating | | 210 | 270 | mA | V _{CC} ≤4.2V _{DC} , P _{OUT} =21dBm, 11b, 50Ω, All Temp |
| V _{REG} | | 3 | 5 | mA | T=25 °C |
| FEM Leakage | | | 500 | nA | V _{CC} ="ON", V _{REG} =0.2V _{DC} , RF OFF |
| V _{REG} Leakage | | | 50 | nA | |
| Noise Figure | | 8 | 9 | dB | |
| Input Return Loss | 8 | 10 | | dB | |
| Thermal Resistance | | 52 | | °C/W | V _{CC} =4.8V, V _{REG} =2.95V, C _{TX} =3.3, C _{RX} =C _{BT} =GND, P _{OUT} =18dBm, Modulation=OFDM 11g, Freq=2.45GHz, DC=100%, T=85 °C |
| Harmonics | | | | | P _{OUT} =21dBm, 1Mbps, CCK BW=1MHz, up to 3:1 load |
| Second | | | -15 | dBm | 4.80GHz to 5.00GHz, V _{CC} =3.3V, Temp=25 °C |
| Third | | | -20 | dBm | 7.20GHz to 7.50GHz, V _{CC} =3.3V, Temp=25 °C |
| Stability | | | | | PA must be stable from 0 dBm to 21dBm. CW Signal, No spurs above -41.25dBm for non-harmonic related signals. |
| Output VSWR | 4:1 | | | | All phase angles, no spurious or oscillations. |
| Ruggedness | | | | | No Damage Conditions over Voltage and Temperature |
| Output VSWR | 10:1 | | | | |
| Input Power | | | 0 | dBm | CW Input Power |
| Input Port Impedance | | 50 | | Ω | |
| Turn-On/Off Time | | | 1 | usec | Output stable to within 90% of final gain |
| 2.4GHz Receive | | | | | |
| Frequency | 2.4 | | 2.5 | GHz | |
| Insertion Loss | | .08 | 1.2 | dB | |
| Input P1dB | 22 | | | dBm | |
| Passband Ripple | | | | | |
| WiFi RX Mode | -0.2 | | +0.2 | dB | |
| WiFi RX/BT Mode | -0.2 | | +0.2 | dB | |
| WiFi RX Port Return Loss | 10 | 12 | | dB | |
| WiFi RX Port Impedance | | 50 | | Ω | |

| Parameter | Specification | | | Unit | Condition |
|----------------------------|---------------|------|------|------|--------------------------------------|
| | Min. | Typ. | Max. | | |
| Bluetooth® | | | | | |
| Frequency | 2.4 | | 2.5 | GHz | |
| Insertion Loss | | 0.8 | 1.2 | dB | |
| Bluetooth Input P1dB | 22 | | | dBm | |
| Bluetooth Port Return Loss | 10 | 12 | | dB | |
| Bluetooth Port Impedance | | 50 | | Ω | |
| Other Requirements | | | | | |
| Antenna Port Impedance | | 50 | | Ω | |
| Return Loss | 10 | 12 | | dB | In WiFi RX or BT Mode |
| Isolation | | | | | |
| ANT to RX | 20 | | | dB | At rated P _{OUT} in TX Mode |
| Switch Control Voltage | | | | | |
| Low | 0 | | 0.2 | V | |
| High | 2.7 | | 3.6 | V | |
| Switch Control Current | | | | | |
| Low | | | 0.5 | uA | |
| High | | | 100 | uA | |
| ESD | | | | | |
| Human Body Model | 1000 | | | V | Pin-Ground |
| Charge Device Model | 500 | | | V | JESD22-C101C, Class III |
| Case Temperature | -10 | | +70 | °C | Full Performance |
| Extreme Case Temperature | -40 | | +85 | °C | Reduced Performance |

Note 1: The PA must operate with gated bias voltage input at 1% to 99% duty cycle.

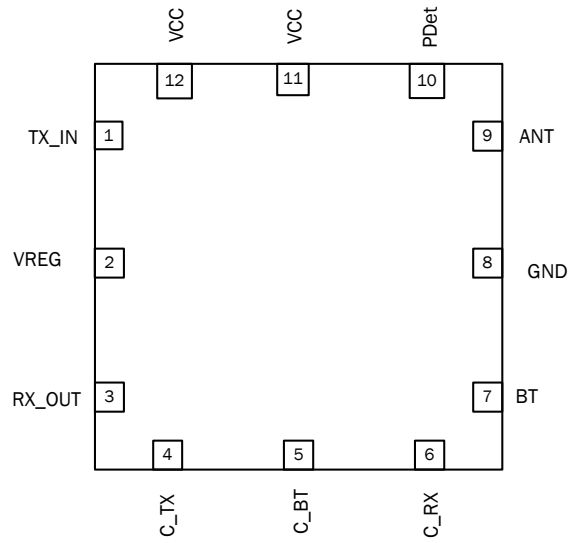
Note 2: The output power for channels 1 and 11 may be reduced to meet FCC restricted band requirements.

Switch Control Logic Truth Table

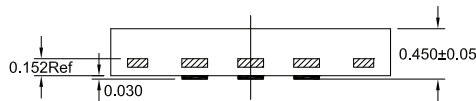
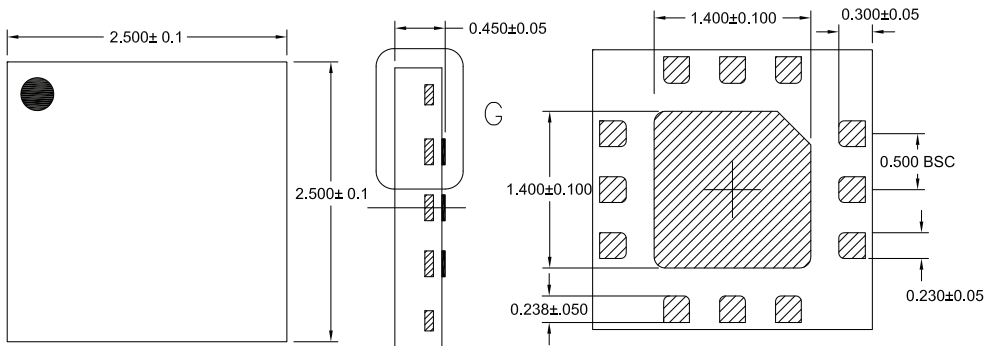
| Mode | C_TX | C_RX | C_BT | VREG |
|--------------|------|------|------|------|
| Transmit | High | Low | Low | High |
| Receive | Low | High | Low | Low |
| Bluetooth | Low | Low | High | Low |
| Simultaneous | Low | High | High | Low |

| Pin | Function | Description |
|-----------------|---------------------|---|
| 1 | TX IN | RF input for the 802.11b/g/n PA. Input is matched to 50Ω. DC block required. |
| 2 | VREG | Regulated voltage for the PA bias control circuit. An external bypass capacitor may be needed on the VREG line for decoupling purposes. |
| 3 | RX OUT | Receive port for 802.11b/g/n band. Internally matched to 50Ω. DC block required. |
| 4 | C_TX | Control pin for WiFi Transmit Port. See truth table for proper settings. |
| 5 | C_BT | Control pin for <i>Bluetooth</i> ® Port. See truth table for proper settings. |
| 6 | C_RX | Control pin for WiFi Receive Port. See truth table for proper settings. |
| 7 | BT PORT | <i>Bluetooth</i> ® RF Port. DC block required. |
| 8 | GND | Ground connection. |
| 9 | ANT | Antenna port matched to 50Ω. DC block required. |
| 10 | POWER DETECT | Power detector voltage for TX section. P _{DET} voltage varies with output power. May need external decoupling. |
| 11 | VCC | Supply voltage for the FEM. See applications schematic for biasing and bypassing components. |
| 12 | VCC | Same as pin 11. |
| Pkg Base | GND | Ground connection. The backside of the package should be connected to the ground plane through a short path, i.e., PCB vias under the device are recommended. |

Pin Out



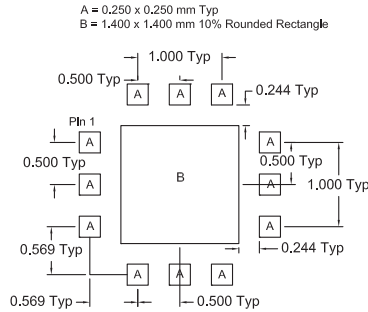
Package Outline Drawing



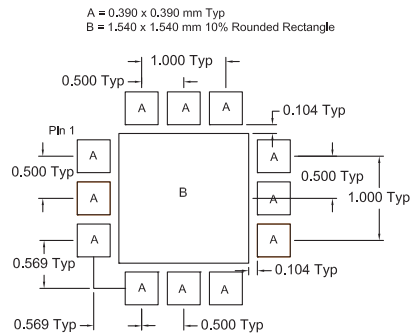
DETAIL G
VIEW ROTATED 90° CLOCKWISE

- 1) PIN 1 INDICATOR SHADED AREA
- 2) CHAMFERED AREA IS PIN 1 INDICATOR

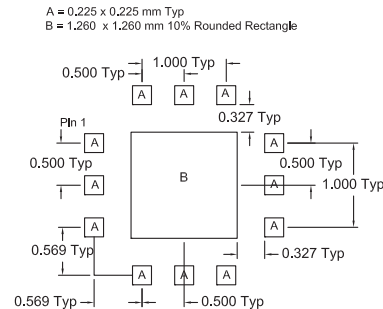
PCB Recommendations



PCB METAL LAND PATTERN



PCB SOLDER MASK LAND PATTERN

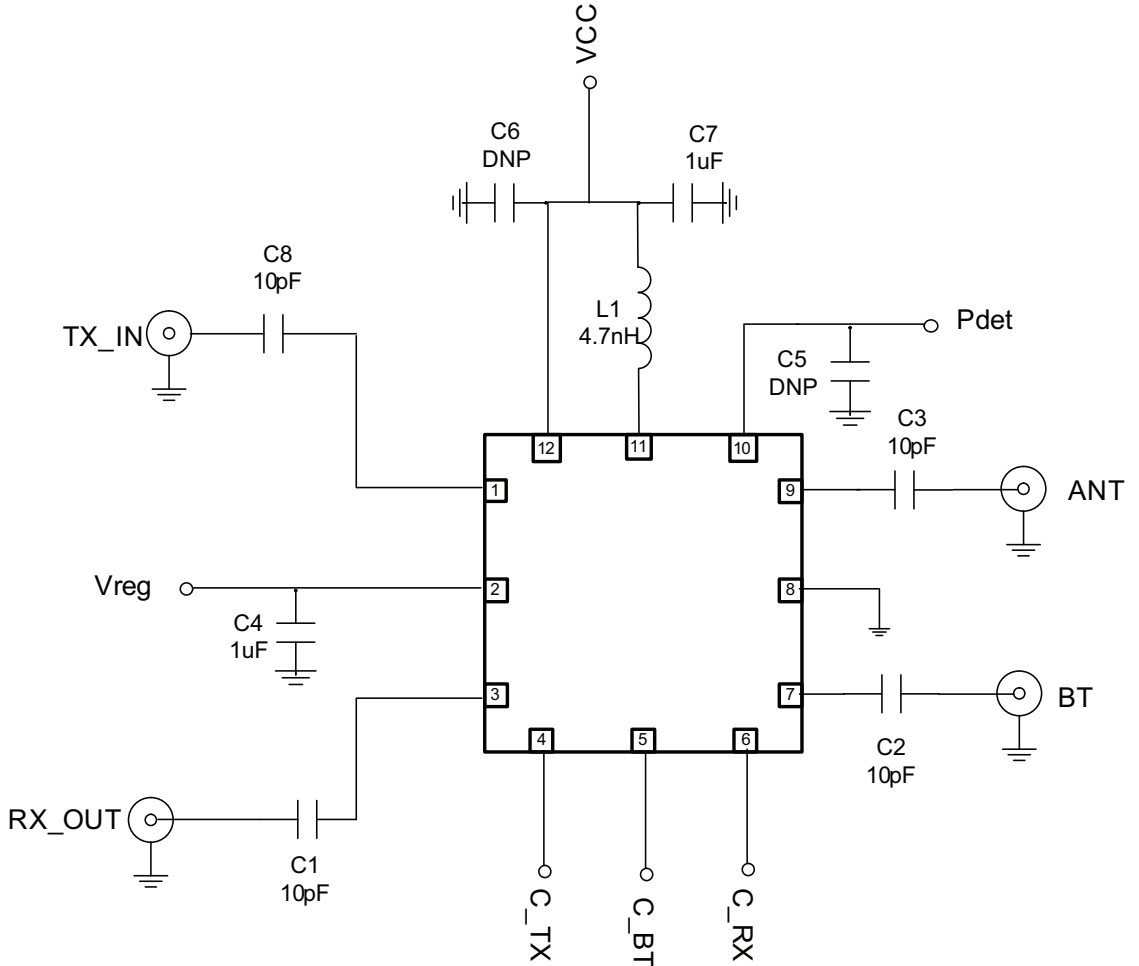


PCB STENCIL PATTERN

PCB land patterns for RFMD components are based on IPC-7351 standards and RFMD empirical data. The pad pattern shown has been developed and tested for optimized assembly at RFMD. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

Thermal vias for center slug "B" should be incorporated into the PCB design. The number and size of thermal vias will depend on the application. Example of the number and size of vias can be found on the RFMD evaluation board layout.

Evaluation Board Schematic

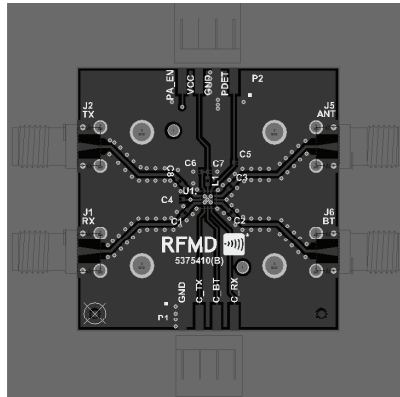


Note: Components C5 and C6 may not be needed in the final schematic. This will be dependent on board layout and noise coupling to these pins. TX input connects directly to the transceiver. If no DC is present on this pin, C8 may also be eliminated.

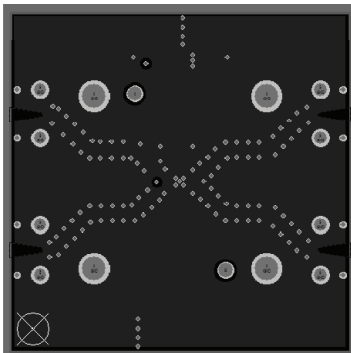
Evaluation Board Layout

Note: For best performance, it is recommended to follow the routing and grounding of the RFMD evaluation board as close as possible. At a minimum, use five ground thermal vias on the package center slug (via size: 12mil hole by 22mil capture pad).

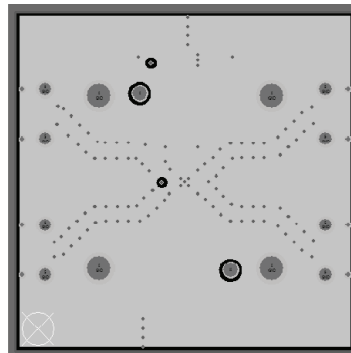
TOP LAYER



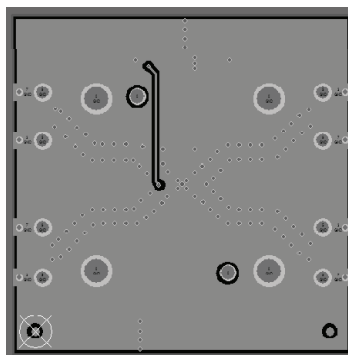
MID LAYER-1



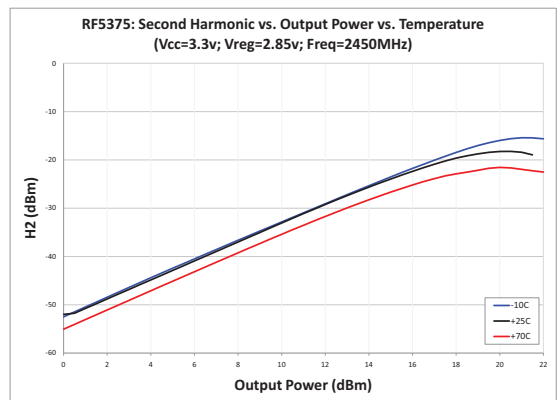
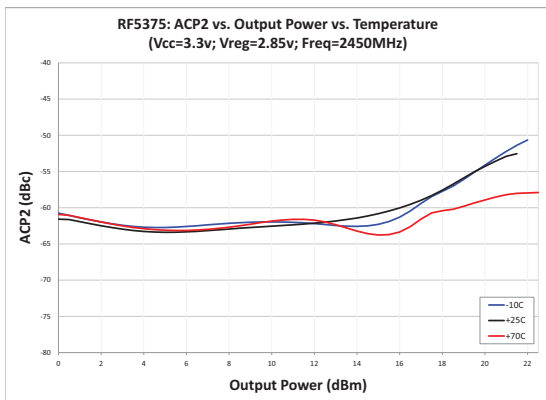
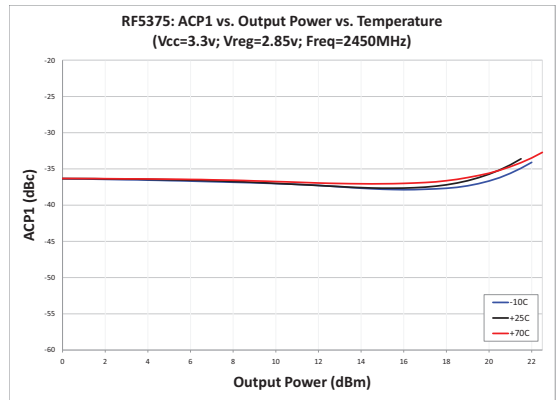
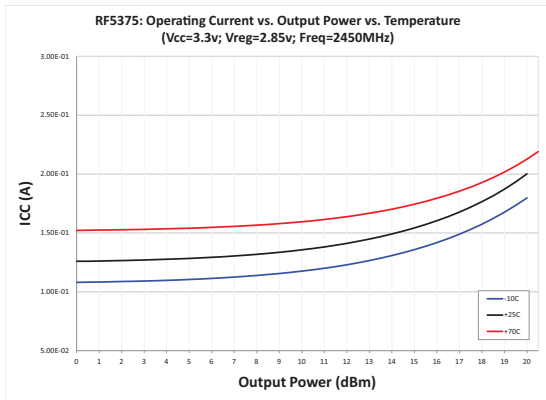
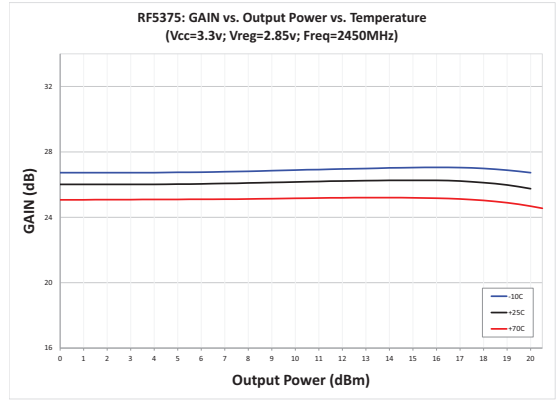
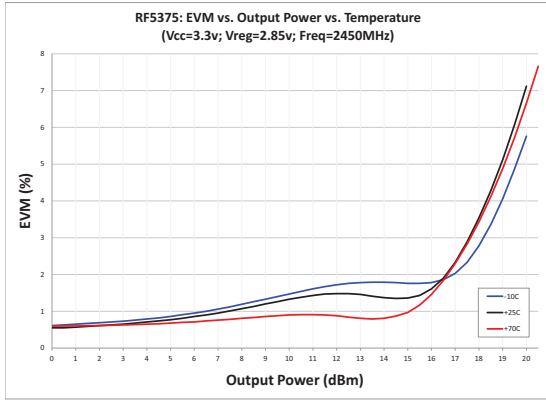
MID LAYER-2



BOTTOM LAYER



Performance Plots



Performance Plots

